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PATENT APPLICATION  
Docket No. 9898-321  
Client No. SS-18146-US

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Ki-Yeon Park, et al. Conf. No. 8248  
Serial No. 10/713,577 Examiner: Not yet assigned  
Filed: November 12, 2003 Art Unit: 2818  
For: CAPACITOR OF SEMICONDUCTOR MEMORY DEVICE  
THAT HAS COMPOSITE Al<sub>2</sub>O<sub>3</sub>/HfO<sub>2</sub> DIELECTRIC  
LAYER AND METHOD OF MANUFACTURING THE  
SAME

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is submitted:

- ☒ under 37 CFR 1.97 (b); or  
(Within three months of filing national application; or date of entry of International application;  
or before mailing date of first office action on the merits; whichever occurs last)
- ☐ under 37 CFR 1.97 (c) together with either a:  
☐ Statement under 37 CFR 1.97 (e), or  
☐ a \$180 fee under 37 CFR 1.17 (p); or  
(After mailing of first Office Action, but prior to Notice of Allowance or Final Office Action)
- ☐ under 37 CFR 1.97 (d) together with:  
☐ Statement under 37 CFR 1.97 (e), and  
☐ a \$180.00 fee set forth in 37 CFR 1.17 (p).  
(Filed after final action or notice of allowance, whichever occurs first, but before payment of

the issue fee)

☒ Applicant(s) submit herewith Form PTO 1449- Information Disclosure Citation together with  
copies of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe(s)  
may be material to the examination of this application and for which there may be a duty to disclose in accordance  
with 37 CFR 1.56.

It is requested that the information disclosed herein be made of record in this application.

Any deficiency or overpayment should be charged or credited to deposit account number 13-1703. A  
duplicate copy of this sheet is enclosed.

Customer No. 20575

Respectfully submitted,

MARGER JOHNSON &amp; McCOLLOM, P.C.

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Angie C. Farr



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INFORMATION DISCLOSURE CITATION  
FORM PTO-1449 (Modified)

FOREIGN PATENT DOCUMENTS

<u>Exam Init</u>	<u>Ref</u>	<u>Publication Number</u>	<u>Publication Date</u>	<u>Country</u>	<u>Name</u>
_____	_____	P2002-0002596	Jan. 10, 2002	Korea	
_____	_____	P2002-0034520	May 9, 2002	Korea	

OTHER DOCUMENTS

<u>Exam Init</u>	<u>Ref</u>	<u>Author, Title, Date, Pertinent Pages, Etc.)</u>
_____	_____	English Language Abstract of Korean Publication No: P2002-0002596
_____	_____	English Language Abstract of Korean Publication No: P2002-0034520

Examiner: \_\_\_\_\_

Date Considered: \_\_\_\_\_